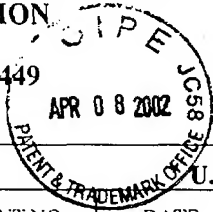
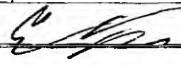
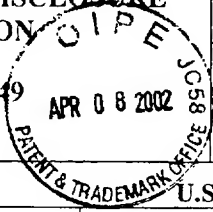




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U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
EF	4,058,430	11/15/77	Suntola et al.	156	611		
EF	4,389,973	6/28/83	Suntola et al.	118	725		
EP	4,413,022	11/1/83	Suntola et al.	427	255.2		
EP	4,416,933	11/22/83	Antson et al.	428	216		
EP	4,533,410	8/6/85	Ogura et al.	148	175		
EP	4,533,820	8/6/85	Shimizu	219	411		
EP	4,689,247	8/25/87	Doty et al.	427	126.1		
EP	4,828,224	5/9/89	Crabb et al.	251	298		
EP	4,836,138	6/6/89	Robinson et al.	118	666		
FOREIGN PATENT DOCUMENTS							
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EF	0 511 264 B1	11/4/92	EP	B01J	37/02	<input type="checkbox"/>	<input type="checkbox"/>
EF	WO 91/10510	7/25/91	PCT	B01J	37/02	<input type="checkbox"/>	<input type="checkbox"/>
	60 10625	1/19/85	JP	H01L	21/302	<input type="checkbox"/>	<input type="checkbox"/>
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EF	Bedair, S.M. et al., "Atomic Layer Epitaxy of III-V Binary Compounds", Appl. Phys. Lett. (1985) 47(1): 51-3						
	Tischler, M.A. et al., "Growth and Characterization of Compound Semiconductors by Atomic Layer Epitaxy", J. Cryst. Growth (1986) 77: 89-94						
EF	Goodman, C. et al., "Atomic Layer Epitaxy", J. Appl. Phys. (1986) 60(3): R65-R81						
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EF	O'Hanlon, J. "Gas Release From Solids", A Users Guide to Vacuum Technology (1989) Chap. 4: 56-71						
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EF	4,846,102	7/11/89	Ozias	118	730		
EF	4,907,862	3/13/90	Suntola	350	345		
EF	4,913,929	4/3/90	Moslehi et al.	427	39		
BF	4,975,252	12/4/90	Nishizawa et al.	422	245		
BF	4,976,996	12/11/90	Monkowski et al.	427	255.5		
EF	4,933,360	2/19/91	Nakamura	118			
EF	5,000,113	3/19/91	Wang et al.	118	723		
EF	5,015,503	5/14/91	Varrin Jr. et al.	427	255.2		
EF	5,077,875	1/7/92	Hoke et al.	29	25.01		
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	5-152215	6/18/93	JP	H01L	21/205	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	8-236459	9/13/96	JP	H01L	21/205	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	10-102256	4/21/98	JP	H01L	16/44	<input type="checkbox"/>	<input checked="" type="checkbox"/>
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EF	Suntola, T. "Atomic Layer Epitaxy", Material Science Reports (1989) 4: 261-312						
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EF	Higashi, G. et al., "Sequential Surface Chemical Reaction Limited Growth of High Quality Al2O3 Dielectrics", Appl. Phys. Lett. (1989) 55(19): 1963-5						
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U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
EF	5,078,851	1/7/92	Nishihata et al.	204	298.4	
EF	5,119,760	6/9/92	McMillan et al.	118	722	
EF	5,156,820	10/20/92	Wong et al.	422	186.05	
EF	5,194,401	3/16/93	Adams et al.	437	173	
EF	5,204,314	4/20/93	Kirlin et al.	505	1	
EF	5,270,247	12/14/93	Sakuma et al.	437	133	
EF	5,281,274	1/25/94	Yoder	118	697	
EF	5,294,778	3/15/94	Carman et al.	219	385	
EF	5,320,680	6/14/94	Learn et al.	118	724	
EF	5,336,327	8/9/94	Lee	118	730	
EF	5,484,484	1/16/96	Yamaga et al.	118	719	
EF	5,582,866	12/10/96	White	427	248.1	
EF	5,693,139	12/2/97	Nishizawa et al.	117	89	
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EF	Roth, A. "The Vacuum", Vacuum Technology (1990) Chap. 1: 1-7 and Chap. 2: 28-45					
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EF	Lubben, D. et al., "UV Photostimulated Si Atomic-Layer Epitaxy", Mat. Res. Soc. Symp. Proc. (1991) 222: 177-187					
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EF	Suntola, T. "Atomic Layer Epitaxy", Thin Solid Films (1992) 216: 84-9					
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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
EF	5,711,811	1/27/98	Suntola et al.	118	711	
EF	5,749,974	5/12/98	Habuka et al.	118	725	
EF	5,788,447	8/4/98	Yonemitsu et al.	414	217	
EF	5,851,849	12/22/98	Comizzoli et al.	438	38	
EF	5,916,365	6/29/99	Sherman	117	92	
EF	5,935,338	8/10/99	Lei et al.	118	725	
EF	6,007,330	12/28/99	Gauthier	432	47	
EF	6,015,590	1/18/00	Suntola et al.	427	255.23	
EF	6,042,652	3/28/00	Hyun et al.	118	719	
EF	6,050,216	4/18/00	Szapucki et al.	118	723	
EF	6,077,775	6/20/00	Stumborg et al.	438	643	
EF	6,090,442	7/18/00	Klaus et al.	427	255.15	
EF	6,139,700	10/31/00	Kang et al.	204	192.17	
EF	6,143,659	11/7/00	Leem	438	688	
EF	6,270,572	8/7/01	Kim et al.	117	93	
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GF	Yarnoff, J. et al., "Atomic Layer Epitaxy of Silicon By Dichlorosilane Studied with Core Level Spectroscopy", J. Vac. Sci. Technol. (1992) A10(4): 2307-7					
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EF	Imai, S. et al., "Atomic Layer Epitaxy of Si Using Atomic H", Thin Solid Films (1993) 225: 168-72					
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EF	Sneh, O. et al., "Sample Manipulator Employing A Gas-Thermal Switch Designed For High Pressure Experiments in an Ultrahigh Vacuum Apparatus" J. Vac. Sci. Technol. (1995) A13(2): 493-6		
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